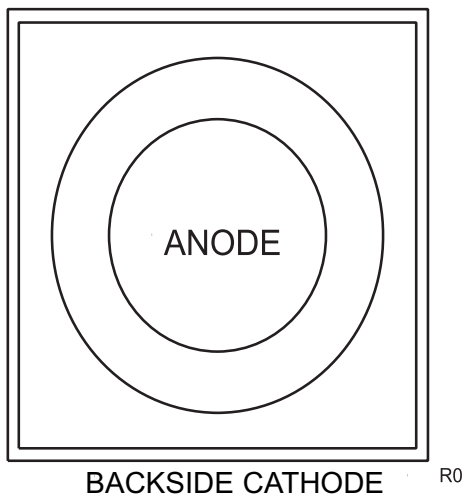


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	17.5 x 17.5 MILS
Die Thickness	8.0 MILS
Anode Bonding Pad Area	8.0 MILS DIAMETER
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 6,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER

34,368

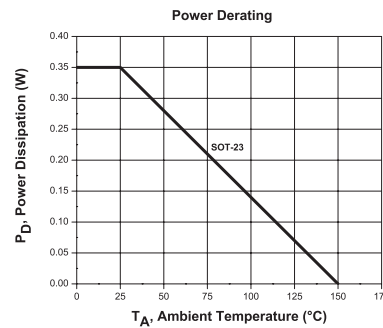
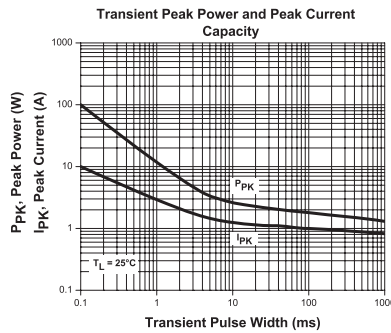
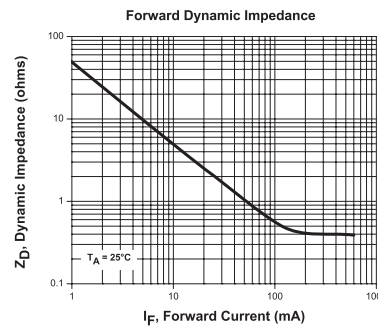
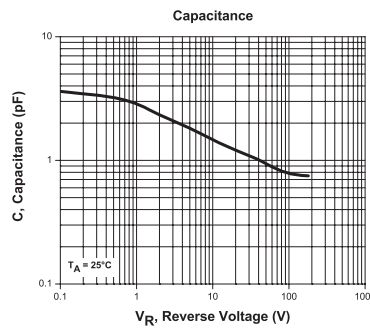
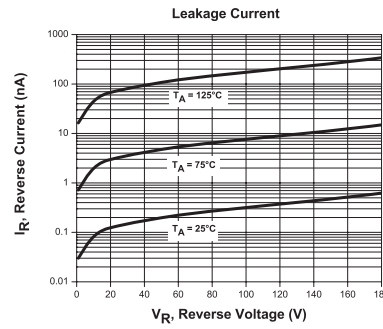
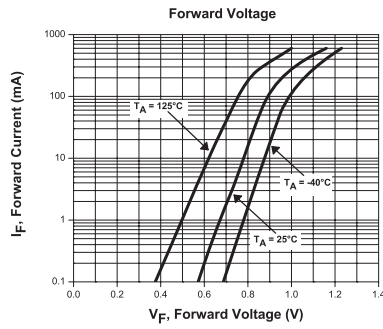
PRINCIPAL DEVICE TYPES

CMPD3003

1N3595

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centalsemi.com

R4 (8-October 2008)



145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centalsemi.com

R4 (8-October 2008)